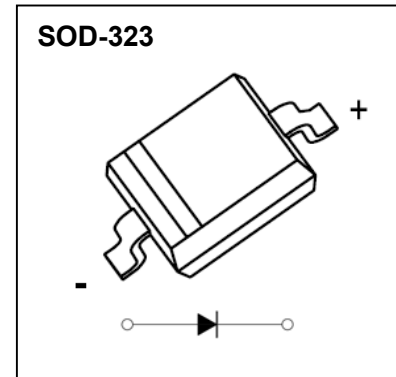
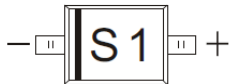


SOD-323 Plastic-Encapsulate Diodes

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Very Low Reverse Capacitance

MARKING: S1



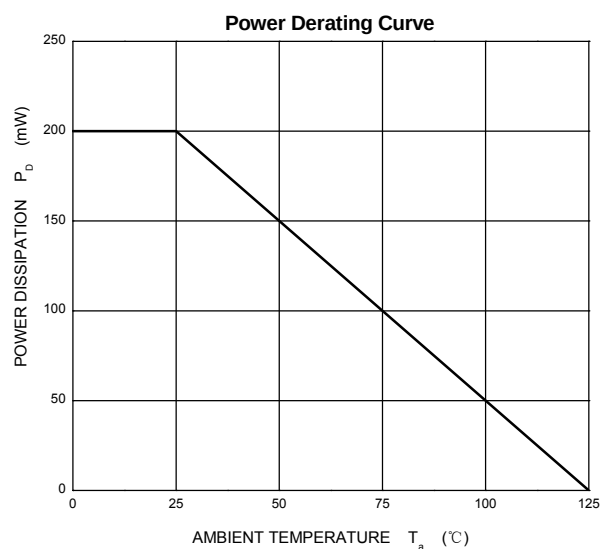
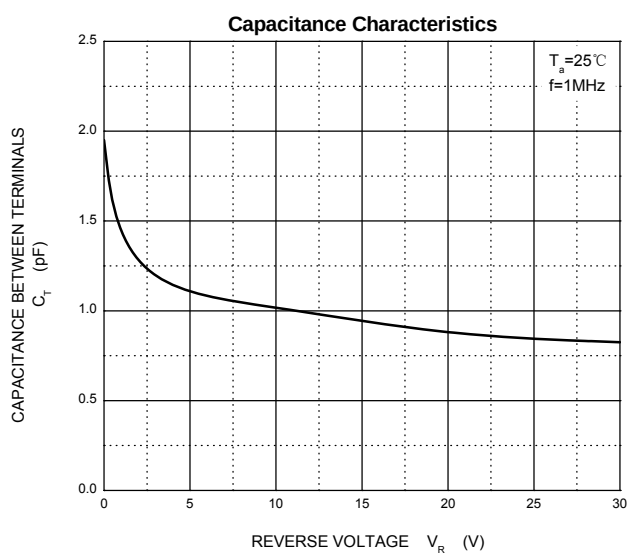
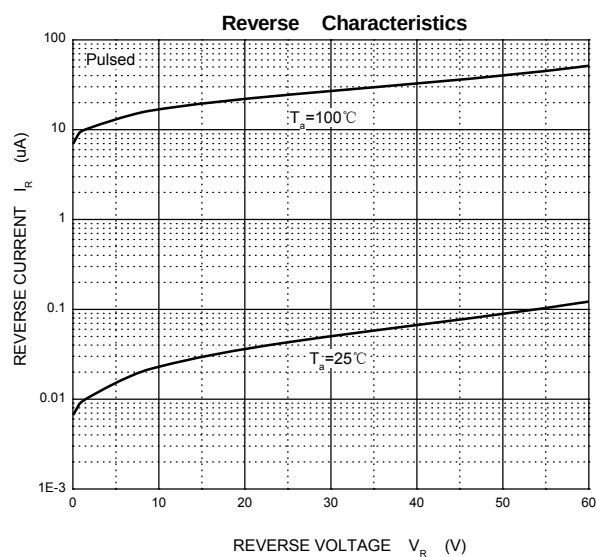
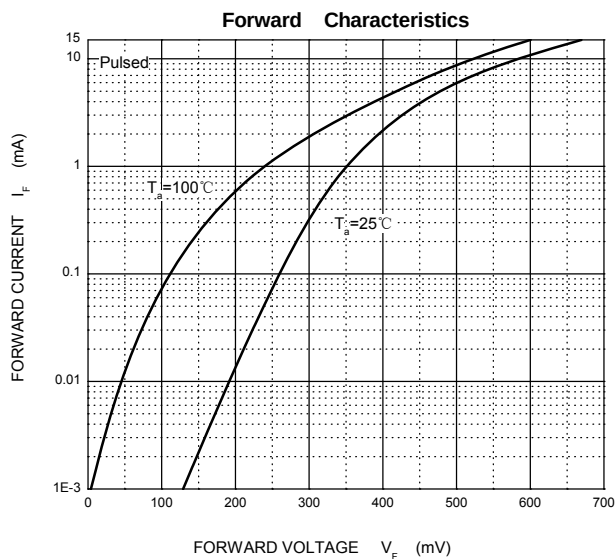
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

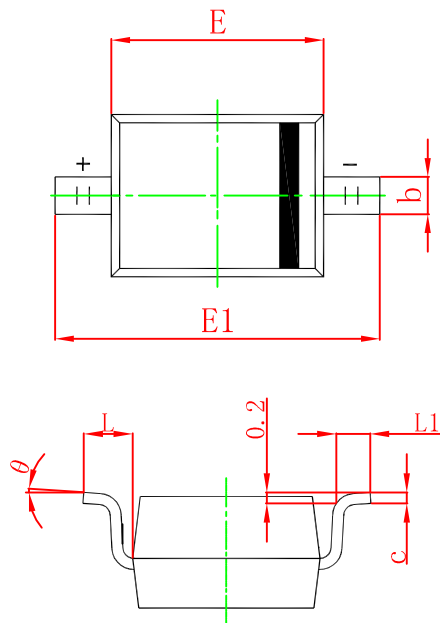
Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	60	V
V_{RWM}	Working Peak Reverse Voltage		
V_R	DC Blocking Voltage		
$V_{R(RMS)}$	RMS reverse voltage	42	V
I_{FM}	Forward Continuous Current	15	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	2	A
P_D	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	500	$^{\circ}\text{C/W}$
T_j	Operating Junction Temperature Range	$-40 \sim +125$	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	$-50 \sim +150$	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=10\mu\text{A}$	60			V
Reverse current	I_R	$V_R=50\text{V}$			0.2	μA
Forward voltage	V_F	$I_F=1\text{mA}$			0.41	V
		$I_F=15\text{mA}$			1	
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F=I_R=5\text{mA}, I_{rr}=0.1 \times I_R, R_L=100\Omega$			1	ns

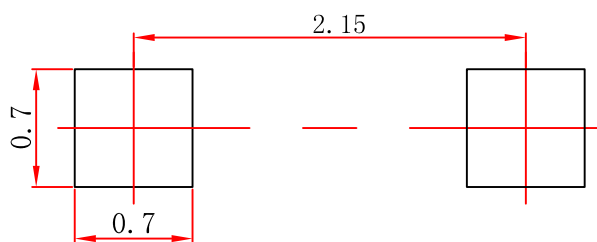
Typical Characteristics





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A		1.100		0.043
A1	0.000	0.100	0.000	0.004
A2	0.800	1.000	0.031	0.039
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.500	2.750	0.098	0.108
L	0.475 REF		0.019 REF	
L1	0.250	0.400	0.010	0.016
θ	0°	8°	0°	8°

SOD-323 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.